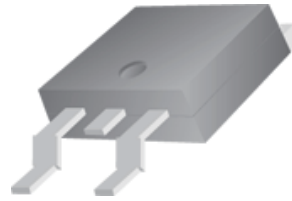


N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology



PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
30	13 @ $V_{GS} = 10V$	51
	20 @ $V_{GS} = 4.5V$	41

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^c	$T_C = 25^\circ\text{C}$ I_D	51	A
Pulsed Drain Current ^b	I_{DM}	195	
Continuous Source Current (Diode Conduction) ^c	$T_C = 25^\circ\text{C}$ I_S	30	A
Power Dissipation ^c	P_D	50	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	$^\circ\text{C/W}$

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature.
- Calculated value shown for reference and for applications where an additional heatsink is used.

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 uA	1.0			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	uA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C			25	
On-State Drain Current ^A	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	34			A
Drain-Source On-Resistance ^A	r _{DS(on)}	V _{GS} = 10 V, I _D = 51 A			13	mΩ
		V _{GS} = 4.5 V, I _D = 41 A			20	
Forward Tranconductance ^A	g _{fs}	V _{DS} = 15 V, I _D = 51 A		22		S
Diode Forward Voltage	V _{SD}	I _S = 34 A, V _{GS} = 0 V		1.1		V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 51 A		12.5		nC
Gate-Source Charge	Q _{gs}			2.6		
Gate-Drain Charge	Q _{gd}			4.6		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 25 V, R _L = 25 Ω , I _D = 34 A, V _{GEN} = 10 V		16		nS
Rise Time	t _r			5		
Turn-Off Delay Time	t _{d(off)}			23		
Fall-Time	t _f			3		

Notes

- Pulse test: $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

Typical Electrical Characteristics

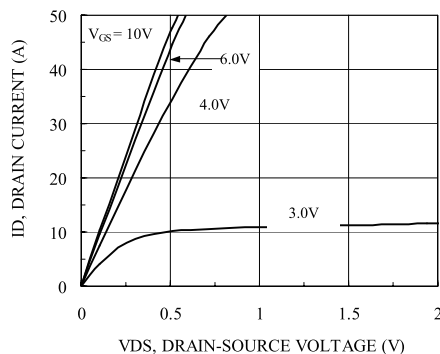


Figure 1. On-Region Characteristics

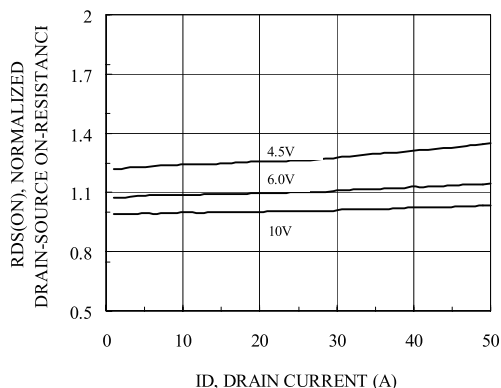


Figure 2. On-Resistance with Drain Current

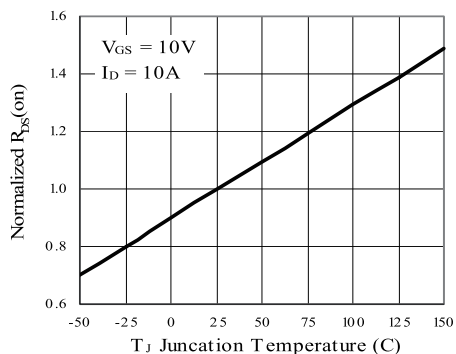


Figure 3. On-Resistance Variation with Temperature

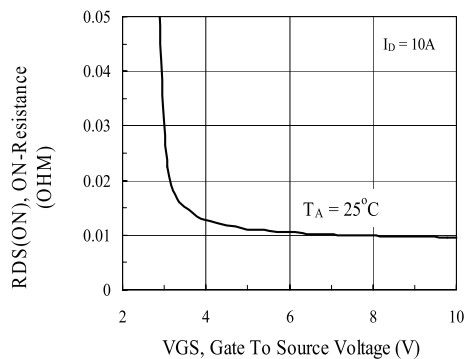


Figure 4. On-Resistance Variation with Gate to Source Voltage

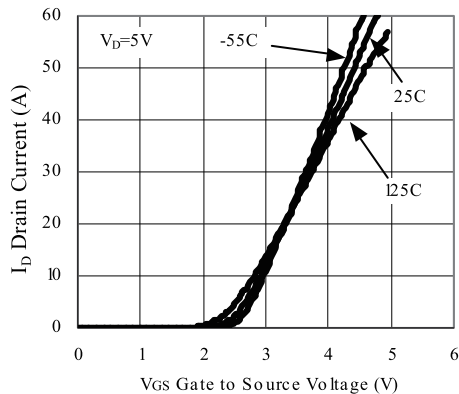


Figure 5. Transfer Characteristics

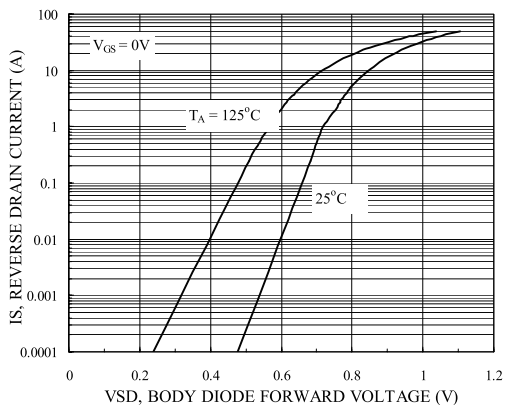


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics

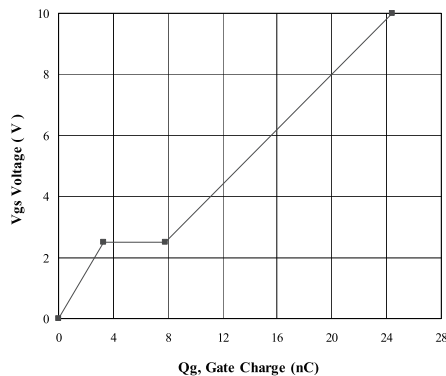


Figure 7. Gate Charge Characteristics

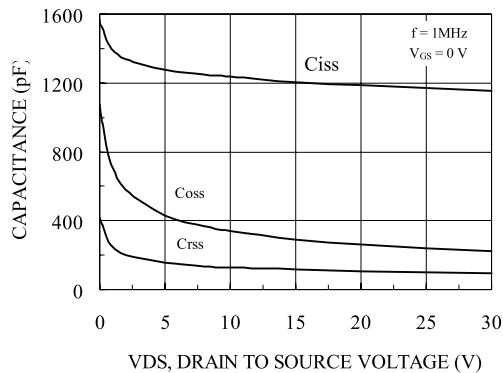


Figure 8. Capacitance Characteristics

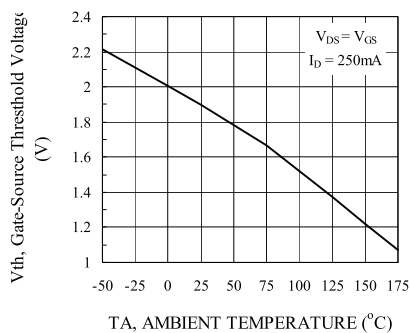


Figure 9. Threshold Vs Ambient Temperature

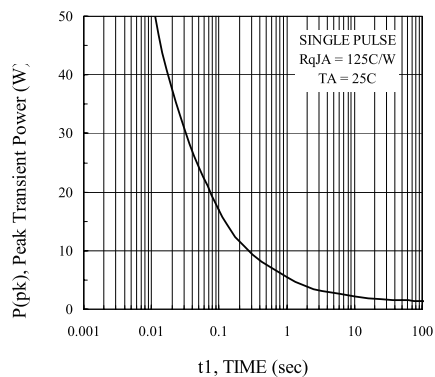


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

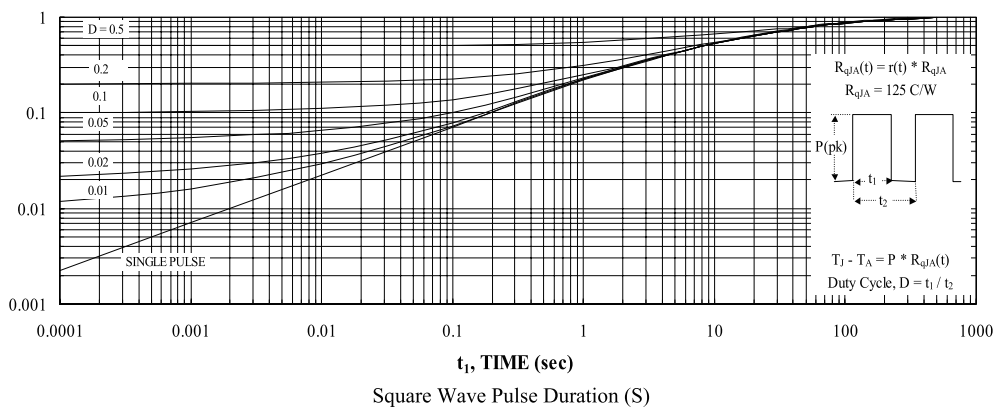
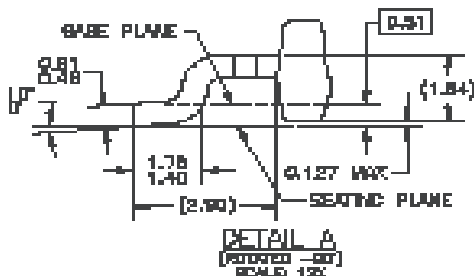
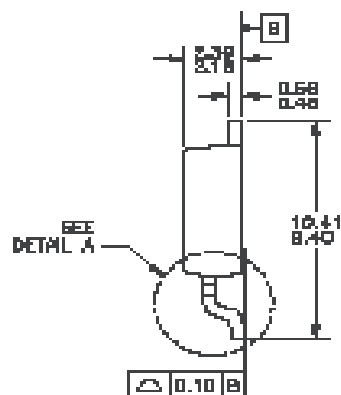
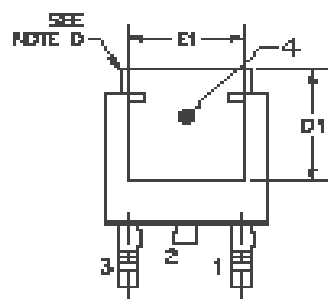
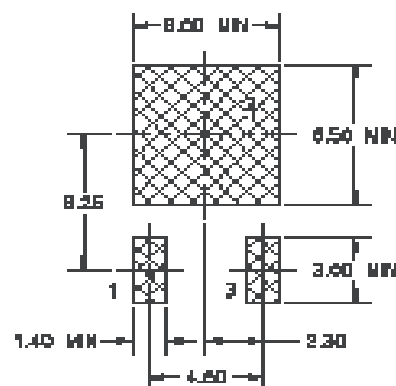
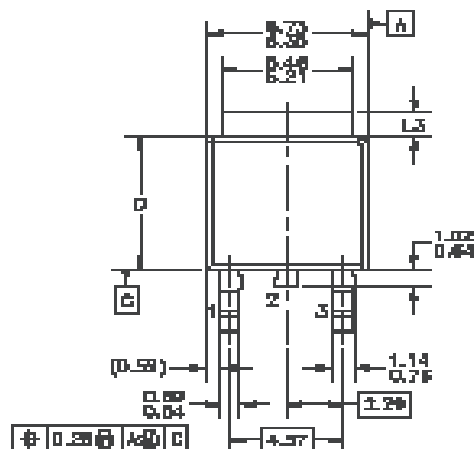


Figure 11. Transient Thermal Response Curve

Package Information



- NOTES: UNLESS OTHERWISE SPECIFIED
- ALL DIMENSIONS ARE IN MILLIMETERS.
 - THIS PACKAGE CONFORMS TO JEDEC, TO-263, ISSUE C, VARIATION AA, 30 DEC, DATED NOV. 1989.
 - DIMENSIONING AND TOLERANCING PER ASME Y14.00M-1984.
 - HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
 - DIMENSIONS L3, D, E1 AND D1 TABLE:

	OPTIONAL A1	OPTIONAL A2
L3	0.68-1.27	1.62-2.52
D	0.92-0.99	0.93-0.99
E1	4.32 MIN	3.81 MIN
D1	3.81 MIN	4.37 MIN